Silicon PNP Power Transistors 2SB1274

DESCRIPTION

·With TO-220F package
·Complement to type 2SD1913
·High reliability.
·High breakdown voltage
·Low saturation voltage.
·Wide area of safe operation

APPLICATIONS

·60V/3A low-frequency power amplifier
·General power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base

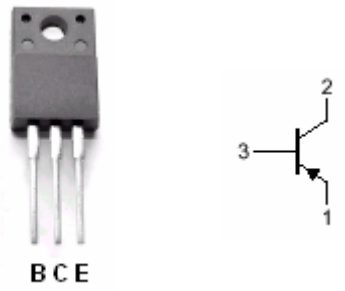

Fig.1 simplified outline (TO-220F) and symbol

Absolute maximum ratings (Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-60	V
V_{CEO}	Collector-emitter voltage	Open base	-60	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-3	A
I_{CM}	Collector current-peak		-8	A
P_C	Collector dissipation	T_C=25□	20	W
			2	
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=-1mA; I_E=0	-60			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-5mA; R_{BE}=∞	-60			V
$V_{(BR)EBO}$	Base-emitter breakdown voltage	I_E=-1mA; I_C=0	-6			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-2A ; I_B=-0.2A		-0.4	-1.0	V
V_{BE}	Base-emitter voltage	I_C=-0.5A ; V_{CE}=-5V		-0.8	-1.0	V
I_{CBO}	Collector cut-off current	V_{CB}=-40V;I_E=0			-0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=-4V;I_C=0			-0.1	mA
h_{FE-1}	DC current gain	I_C=-0.5A ; V_{CE}=-5V	70		280	
h_{FE-2}	DC current gain	I_C=-3A ; V_{CE}=-5V	20			
f_T	Transition frequency	I_C=-0.5A ; V_{CE}=-5V		100		MHz
C_{OB}	Output capacitance	I_E=0; V_{CB}=-10V;f=1MHz		60		pF

◆ **h_{FE-1} classifications**

Q	R	S
70-140	100-200	140-280

PACKAGE OUTLINE

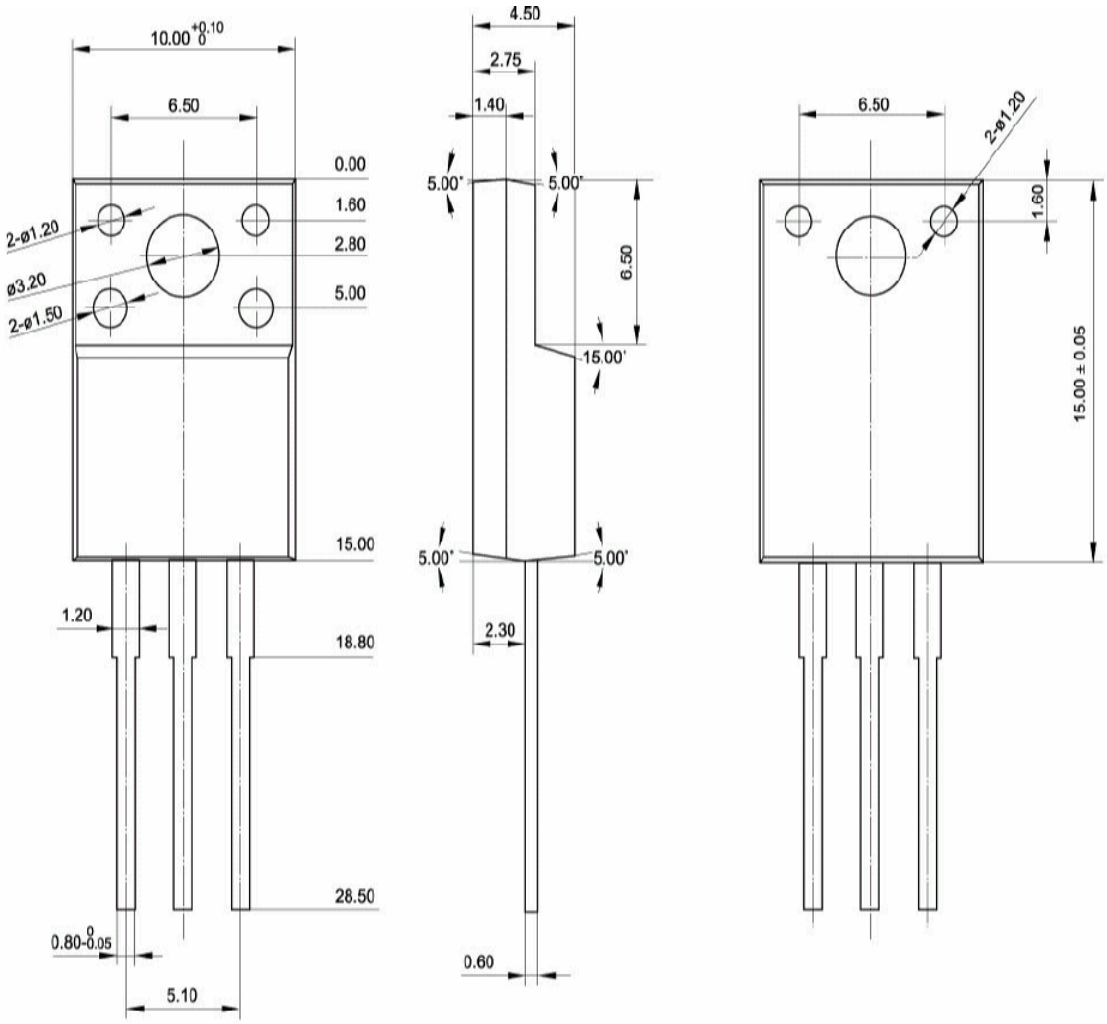

Fig.2 Outline dimensions

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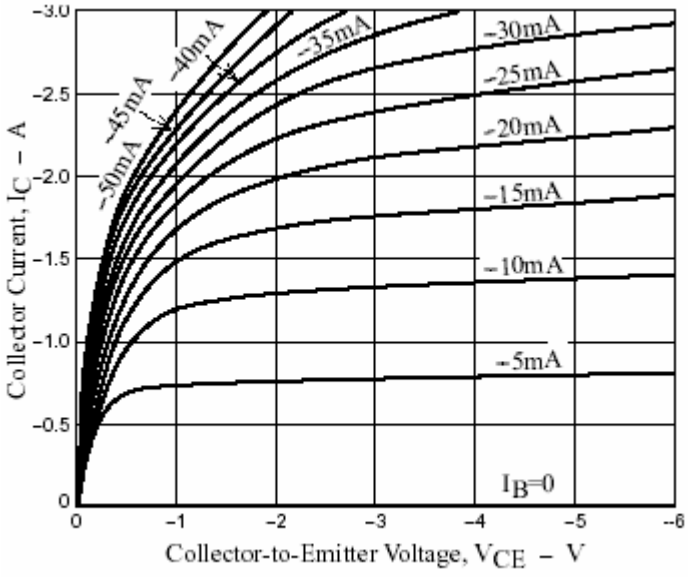

Fig.3 Static Characteristic

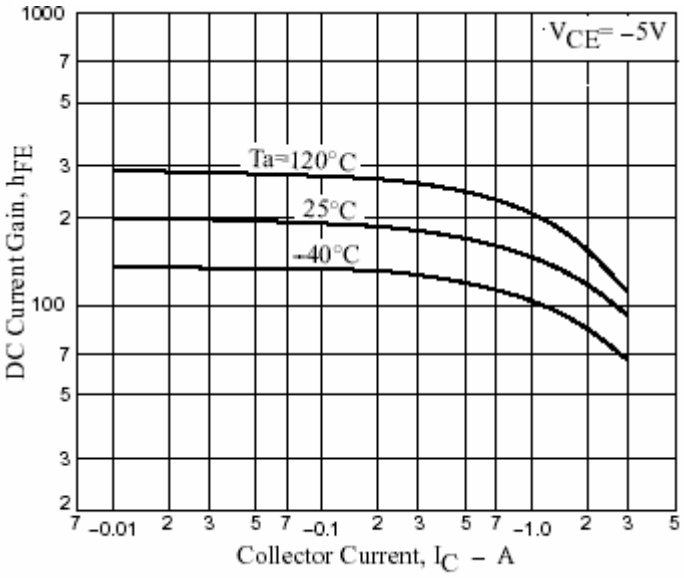

Fig.4 DC current Gain

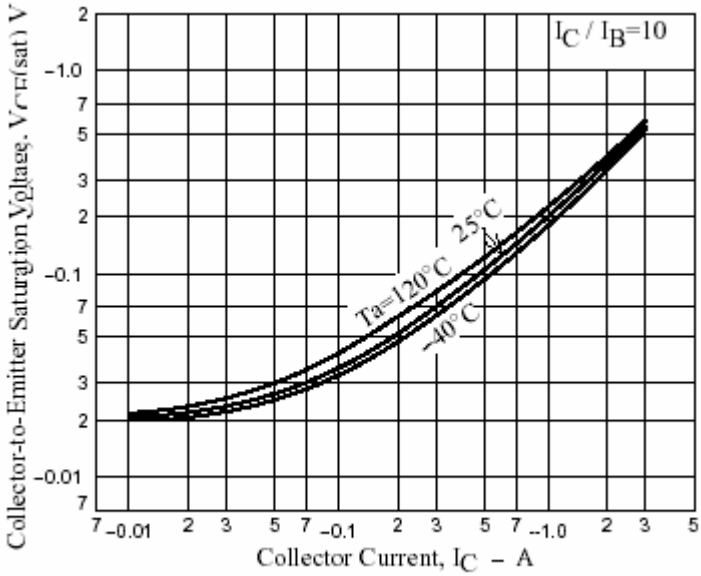

Fig.5 Collector-Emitter Saturation Voltage

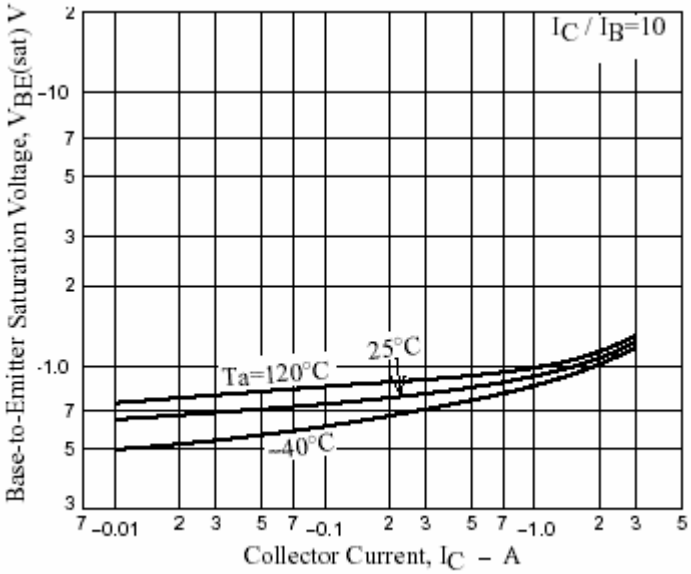

Fig.6 Base-Emitter Saturation Voltage

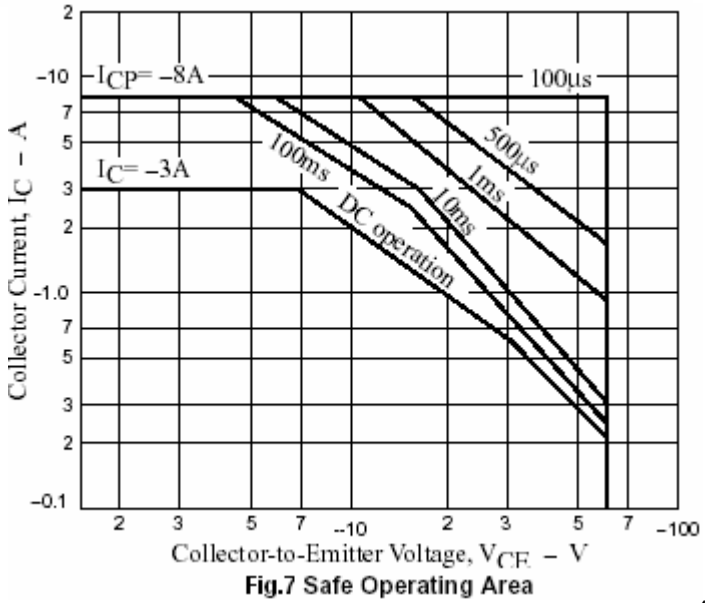

Fig.7 Safe Operating Area